

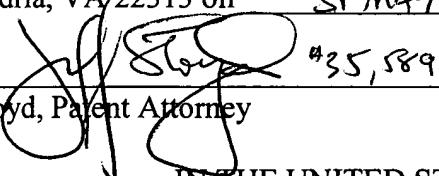


10/750250

CFC

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:  
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Jeff Lloyd, Patent Attorney



435,589

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322  
Docket No. SUN-DA-135T  
Patent No. 7,008,856

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Chang Hun Han  
Issued : March 7, 2006  
Patent No. : 7,008,856  
For : Method for Fabricating AND-Type Flash Memory Cell

Mail Stop Certificate of Corrections Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Certificate  
JUN 08 2006  
of Correction,

REQUEST FOR CERTIFICATE OF CORRECTION  
UNDER 37 CFR 1.323 (APPLICANT MISTAKE)

Sir:

A Certificate of Correction (in duplicate) for the above-identified patent has been prepared and is attached hereto.

In the left-hand column below is the column and line number where error occurred in the patent. In the right-hand column is the page and line number in the application where the correct information should have appeared.

Patent Reads:

Column 1, line 34:

“pattern 15”

Application Should Read:

Page 1, lines 4 of [0004]:

--pattern 17--

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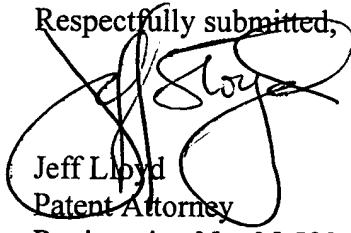
01 FC:1811 100.00 DA

A true and correct copy of page 1 of the specification as filed accompanies this Certificate of Correction, showing the typographical error at line 4 of [0004] and the correct information at line 3 of [0005].

The Commissioner is authorized to charge the fee of \$100.00 for the amendment to Deposit Account No. 19-0065. The Commissioner is also authorized to charge any additional fees as required under 37 CFR 1.20(a) to Deposit Account No. 19-0065. Two copies of this letter are enclosed for Deposit Account authorization.

Approval of the Certificate of Correction is respectfully requested.

Respectfully submitted,

  
Jeff Lloyd  
Patent Attorney

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JL/fes

Attachments: Copy of page 1 of the specification

UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

PATENT NO. : 7,008,856

Page 1 of 1

APPLICATION NO.: 10/750,250

DATED : December 31, 2003

INVENTORS : Chang Hun Han, Bong Kil Kim

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1,

Line 34, "pattern 15" should read --pattern 17--.

MAILING ADDRESS OF SENDER:  
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JUN 8 2006

METHOD FOR FABRICATING AND-TYPE FLASH MEMORY CELL  
FIELD OF THE DISCLOSURE

[0001] The present disclosure relates generally to semiconductor devices and, more particularly, to a method for manufacturing an AND type flash memory device.

BACKGROUND

[0002] In fabricating a flash memory device, the cell array is an important factor determining a type of a flash memory device together with a memory device structure, an erasing method, and a programming method. Among various cell array structures, AND-type cell arrays can embody the density and the high-performance operation of a flash memory.

[0003] Fig. 1 is a schematic diagram illustrating a cell array of a conventional AND-type flash memory device. The conventional AND-type flash memory device embodies densification (i.e., greater density) by sharing bit line contacts and source lines in a plurality of cells and suppresses the occurrence of disturbances during program operation through parallel connection and the layered bit lines and source lines. However, a conventional AND-type flash memory device has a shortcoming in that interconnection density in a diffusion layer is high.

[0004] Figs. 2a through 2h illustrate, in cross-sectional views, the fabricating process of an AND-type flash memory device according to a conventional method. Referring to Fig. 2a, a pad oxide layer 13 and a pad nitride layer 15 are deposited in sequence on a silicon substrate 11. Then, a photoresist pattern 15 is formed on the pad nitride layer 15.

[0005] Referring to Fig. 2b, some part of the pad nitride layer 15, the pad oxide layer 13, and the substrate 11 is removed by an etching process using the photoresist pattern 17 as a mask. As a result, a pad oxide pattern 13a and a pad nitride pattern 15a